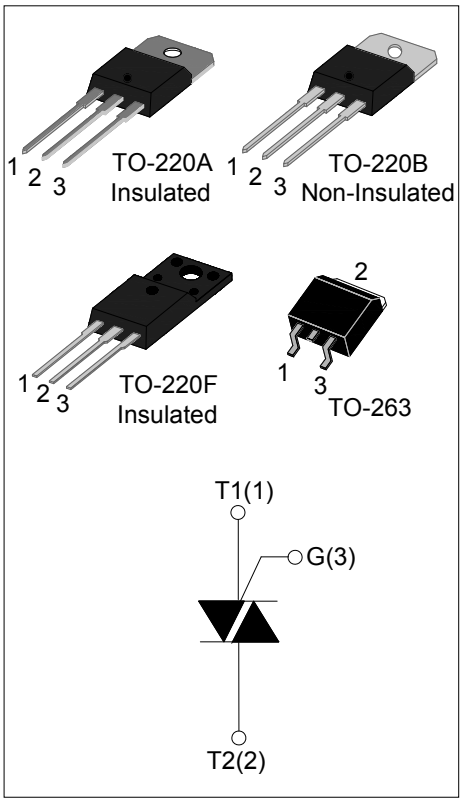
JST16 Series 16A TRIACs

Rev.5.0

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST16 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load. From all three terminals to external heatsink, JST16A provides a rated insulation voltage of 2500 V_{RMS}, and JST16F provides a rated insulation voltage of 2000V_{RMS}, complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} /V_{RRM}	600 and 800 and 1200	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	℃
Operating junction temperature range		T_j	-40-125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	600/800/1200	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	600/800/1200	V
Non repetitive surge peak Off-state voltage		V_{DSM}	V_{DRM} +100	V
Non repetitive peak reverse voltage		V_{RSM}	V_{RRM} +100	V
RMS on-state current	TO-220A(Ins) (T_C=86℃)	$I_{T(RMS)}$	16	A
	TO-220B(Non-Ins) (T_C=107℃)			
	TO-220F(Ins) (T_C=90℃)			
	TO-263 (T_C=80℃)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	160	A

I^2t value for fusing (tp=10ms)	I^2t	128	A^2s
Critical rate of rise of on-state current (I_G =2×I_{GT})	dI/dt	50	A/μs
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value				Unit
				BW	CW	SW	TW	
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	50	35	10	5	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX	1.3				V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	Ⅰ-Ⅱ-Ⅲ	MIN	0.2				V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX	70	50	30	15	mA
		Ⅱ		80	60	40	20	
I_H	I_T =100mA		MAX	60	40	25	15	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j =125℃		MIN	1000	500	200	100	V/μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit
				B	C	
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	50	25	mA
		Ⅳ		70	50	
V_{GT}		ALL	MAX	1.5		V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	ALL	MIN	0.2		V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ-Ⅳ	MAX	70	50	mA
		Ⅱ		100	80	
I_H	I_T =100mA		MAX	60	40	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	500	200	V/μs

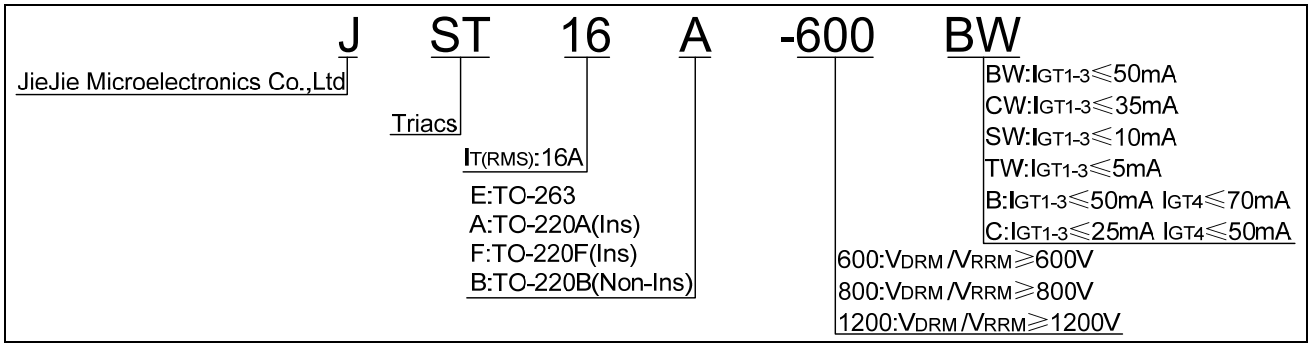
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)			Unit
			-600V	-800V	-1200V	
V_{TM}	I_{TM} =22.5A tp=380μs	T_j=25℃	1.5			V
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25℃	5	5	10	μA
I_{RRM}		T_j=125℃	2	2	1	mA

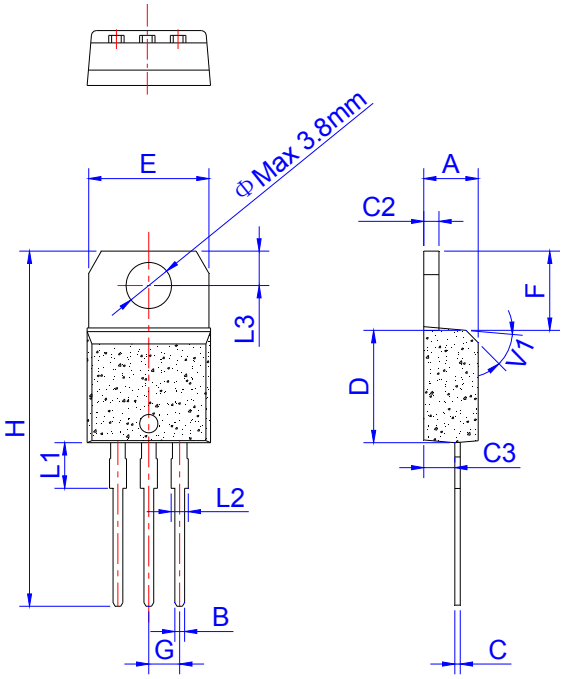
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	2.1	℃/W
		TO-220B(Non-Ins)	1.2	
		TO-220F(Ins)	2.3	
		TO-263	2.5	

ORDERING INFORMATION

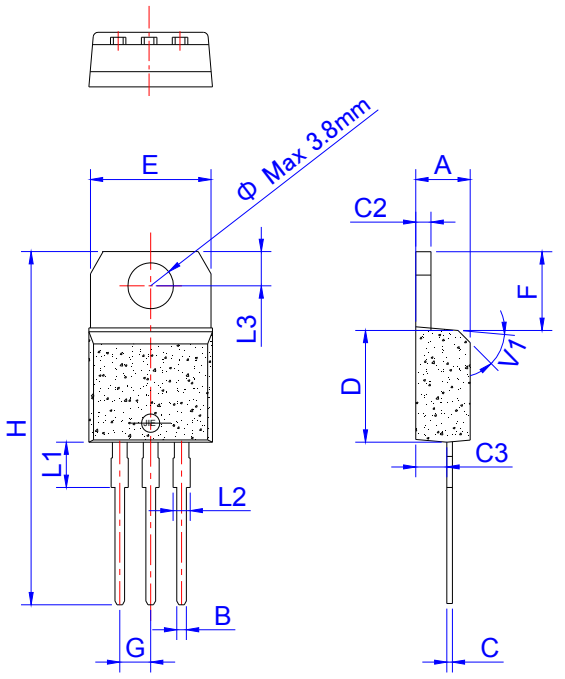


PACKAGE MECHANICAL DATA



TO-220A Ins

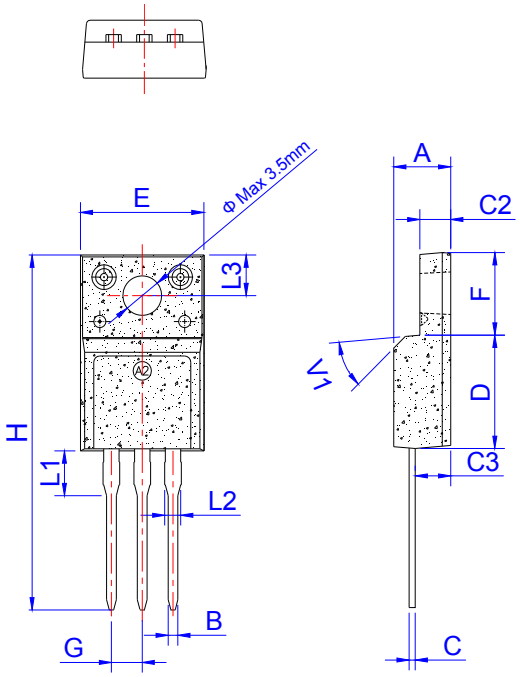
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220B Non-Ins

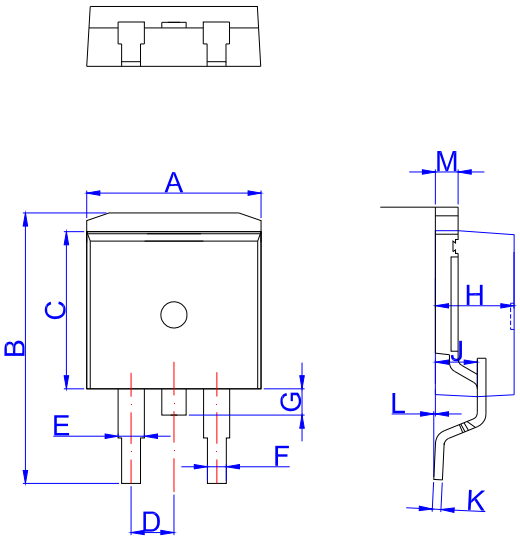
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FIG.1 Maximum power dissipation versus RMS on-state current

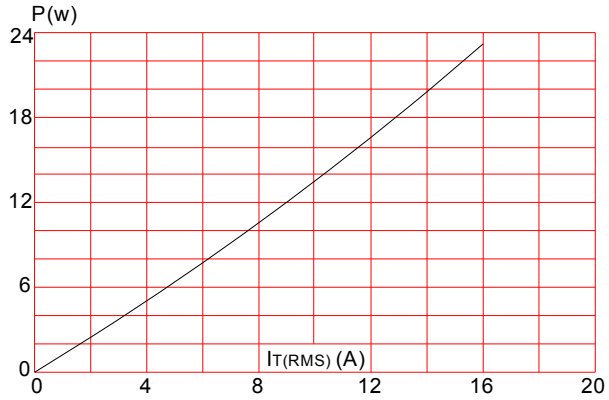


FIG.2: RMS on-state current versus case temperature

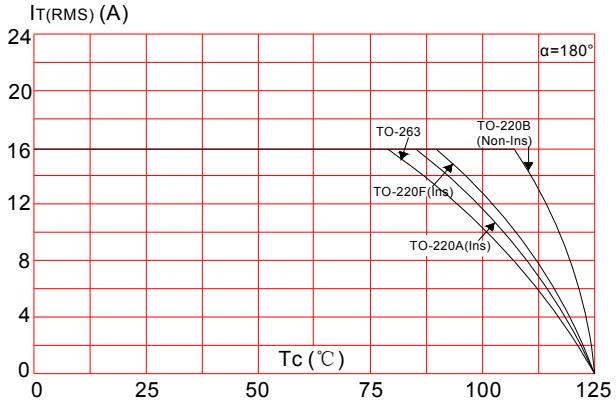


FIG.3: Surge peak on-state current versus number of cycles

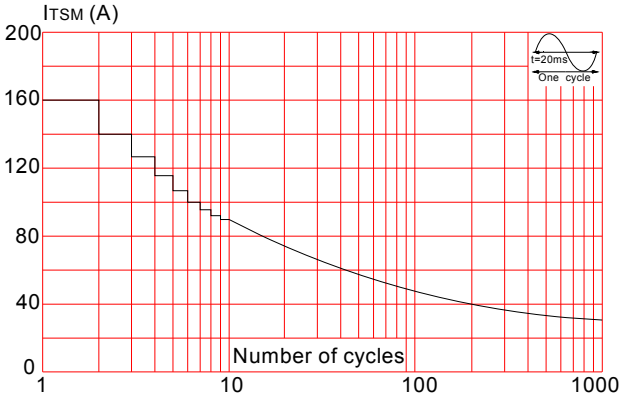


FIG.4: On-state characteristics (maximum values)

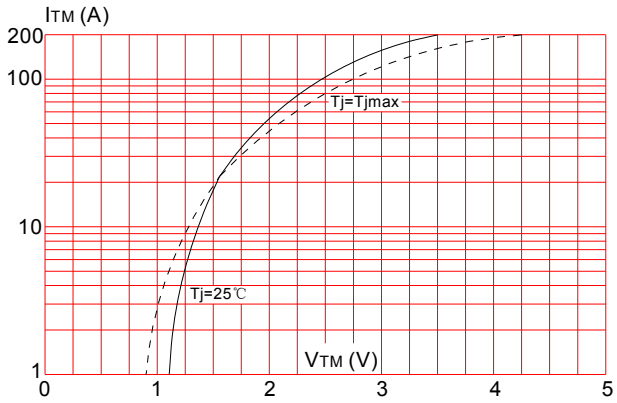


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt < 50A/μs)

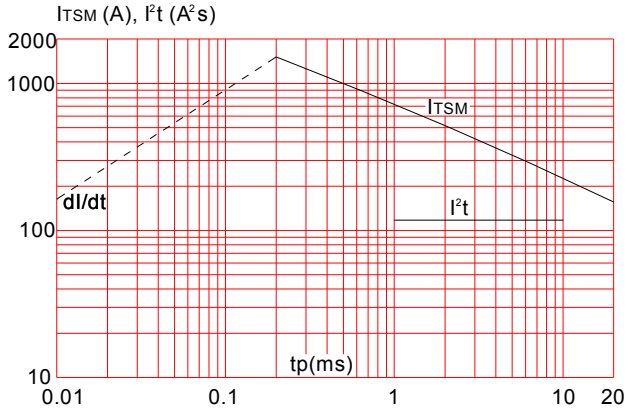
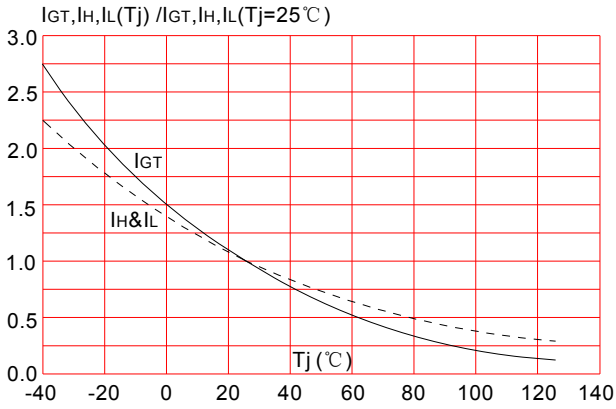


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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